Sam Nyung Yi

List of Publications by Year
in descending order

70	501	933447 10	752698 20
papers	citations	h-index	g-index

70	70	70	649
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A high output magneto-mechano-triboelectric generator enabled by accelerated water-soluble nano-bullets for powering a wireless indoor positioning system. Energy and Environmental Science, 2019, 12, 666-674.	30.8	89
2	Changes in the Raman spectra of monolayer MoS₂ upon thermal annealing. Journal of Raman Spectroscopy, 2018, 49, 1938-1944.	2.5	42
3	Enhanced magnetic energy harvesting properties of magneto-mechano-electric generator by tailored geometry. Applied Physics Letters, 2016, 109, .	3.3	40
4	Charge Transport in Thick Reduced Graphene Oxide Film. Journal of Physical Chemistry C, 2015, 119, 28685-28690.	3.1	35
5	Transition of graphene oxide-coated fiber bundles from insulator to conductor by chemical reduction. Synthetic Metals, 2015, 204, 90-94.	3.9	29
6	Exceeding 50ÂmW RMSâ€Output Magnetoâ€Mechanoâ€Electric Generator by Hybridizing Piezoelectric and Electromagnetic Induction Effects. Advanced Functional Materials, 2022, 32, .	14.9	22
7	Multiscale surface modified magneto-mechano-triboelectric nanogenerator enabled by eco-friendly NaCl imprinting stamp for self-powered IoT applications. Nanoscale, 2021, 13, 8418-8424.	5.6	21
8	A GaN nanoneedle inorganic/organic heterojunction structure for optoelectronic devices. Materials Letters, 2013, 91, 191-194.	2.6	20
9	Oxygen plasma effects on the electrical conductance of single-walled carbon nanotube bundles. Journal Physics D: Applied Physics, 2010, 43, 305402.	2.8	18
10	Energy storage characteristics of {001} oriented Pb(Zr0.52Ti0.48)O3 thin film grown by chemical solution deposition. Thin Solid Films, 2018, 660, 434-438.	1.8	15
11	Enhancing SERS Intensity by Coupling PSPR and LSPR in a Crater Structure with Ag Nanowires. Applied Sciences (Switzerland), 2021, 11, 11855.	2.5	11
12	Growth of AlN layer on patterned sapphire substrate by hydride vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FC02.	1.5	10
13	Hybrid device based on GaN nanoneedles and MEH-PPV/PEDOT:PSS polymer. Materials Research Bulletin, 2015, 68, 326-330.	5.2	8
14	Homogeneity and tolerance to heat of monolayer MoS2 on SiO2 and h-BN. RSC Advances, 2018, 8, 12900-12906.	3.6	8
15	Changes in the Photoluminescence of Monolayer and Bilayer Molybdenum Disulfide during Laser Irradiation. ACS Omega, 2020, 5, 7903-7909.	3.5	8
16	Harvesting electrical energy using plasmon-enhanced light pressure in a platinum cut cone. Optics Express, 2021, 29, 35161.	3.4	8
17	Composite-fermion excitations and the electronic spectra of fractional quantum Hall systems. Physical Review B, 1996, 53, 9599-9601.	3.2	7
18	Thick AlN epilayer grown by using the HVPE method. Journal of the Korean Physical Society, 2015, 67, 643-647.	0.7	7

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19	Effects of P3HT concentration on the electrical properties of the Au/PEDOT:PSS/P3HT/n-GaN hybrid junction structure. Journal of the Korean Physical Society, 2017, 71, 349-354.	0.7	7
20	Theory of direct-interband-transition line shapes based on Moriâ€™s method. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1987, 9, 927-939.	0.4	6
21	Fabrication of n-GaN/MDMO-PPV hybrid structures for optoelectronic devices. Journal of Luminescence, 2014, 147, 1-4.	3.1	6
22	Cyclotron transition linewidths due to electron-phonon interaction via piezoelectric scattering. Journal of Physics Condensed Matter, 1990, 2, 3515-3527.	1.8	5
23	AlN and AlGaN layers grown on Si(111) substrate by mixed-source hydride vapor phase epitaxy method. Japanese Journal of Applied Physics, 2017, 56, 01AD07.	1.5	5
24	Mechanism of light emission and manufacturing process of vertical-type light-emitting diode grown by hydride vapor phase epitaxy. Japanese Journal of Applied Physics, 2017, 56, 01AD03.	1.5	5
25	Fabrication and Time-Dependent Analysis of Micro-Hole in GaAs(100) Single Crystal Wafer Using Wet Chemical Etching Method. Korean Journal of Materials Research, 2019, 29, 155-159.	0.2	5
26	Effect of coupling crater structure and Ag nanoparticles on SERS enhancement. Journal of Materials Science, 2022, 57, 7547-7555.	3.7	5
27	Strain relaxation effect on electronic properties of compressively strained InGaAs/InP vertically stacked multiple quantum wires. Journal of Applied Physics, 2010, 108, 023104.	2.5	4
28	Evolution of GaN nanoflowers from AlNâ€“SiO2 grains on a silicon substrate by chemical vapor reaction. Vacuum, 2011, 86, 201-205.	3.5	4
29	Development of the Hybrid Conjugated Polymer Solar Cell Based on GaN Quantum Dots. Japanese Journal of Applied Physics, 2013, 52, 01AD02.	1.5	4
30	Fabrication of selective-area growth InGaN LED by mixed-source hydride vapor-phase epitaxy. Japanese Journal of Applied Physics, 2018, 57, 01AD03.	1.5	4
31	Comparison of GaN Nanoneedle Structures Formed by Using the HVPE Method. Journal of the Korean Physical Society, 2011, 58, 1351-1355.	0.7	4
32	Validity of the perturbative expansions in the theories of cyclotron resonance lineshape. European Physical Journal B, 1984, 54, 99-102.	1.5	3
33	Optical Gain in Wurtzite ZnO/ZnMgO Quantum Well Lasers. Japanese Journal of Applied Physics, 2005, 44, L1403-L1406.	1.5	3
34	Molecular detection based on the electrical conductance of gold nanoparticle arrays. Sensors and Actuators B: Chemical, 2011, 156, 990-993.	7.8	3
35	Characterization of the InGaN/GaN Multi-Quantum-Wells Light-Emitting Diode Grown on Patterned Sapphire Substrate with Wide Electroluminescence Spectrum. Japanese Journal of Applied Physics, 2011, 50, 01AD06.	1.5	3
36	Verticalâ€Type Blue Light Emitting Diode by Mixedâ€Source Hydride Vapor Phase Epitaxy Method. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700491.	1.8	3

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37	Growth of AlN Epilayers on Sapphire Substrates by Using the Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2019, 74, 1160-1165.	0.7	3
38	Current-voltage Characteristics of PEDOT:PSS/GaN Hybrid-junction Devices with Various Thicknesses of the PEDOT:PSS Layers. New Physics: Sae Mulli, 2014, 64, 1072-1076.	0.1	3
39	Crystal Orientation of GaN Nanostructures Grown on Al$_{2}$O$_{3}$ and Si(111) with a Zr Buffer Layer. Japanese Journal of Applied Physics, 2012, 51, 01AF04.	1.5	2
40	A Detailed Investigation of the Growth Conditions of Gallium Nitride Nanorods by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 01AF05.	1.5	2
41	Finite-difference time-domain analysis of local electric field enhancement by nanoholes of varying shape and diameter in metal with different thicknesses. Japanese Journal of Applied Physics, 2018, 57, 122001.	1.5	2
42	Growth of an AlN Epilayer by Using Mixed-Source Hydride Vapor Phase Epitaxy. New Physics: Sae Mulli, 2018, 68, 39-45.	0.1	2
43	Insights into the growth of hexagonal Si crystals using Al-based nano absorber. Semiconductor Science and Technology, 2022, 37, 045016.	2.0	2
44	Derivation of correlation spectra by the operator algebra technique. Journal of Mathematical Physics, 1992, 33, 336-342.	1.1	1
45	Application of operator algebra technique to some problems in condensed matter physics. Canadian Journal of Physics, 1994, 72, 596-600.	1.1	1
46	Application of a continued-fraction-based theory to magneto-optical intraband transition in GaAs and CdS. Current Applied Physics, 2003, 3, 491-494.	2.4	1
47	Optical gain of compressively strained InGaAs/InP multiple quantum wires. Semiconductor Science and Technology, 2011, 26, 075013.	2.0	1
48	Nonphosphor White Light Emitting Diodes by Mixed-Source Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 01AG06.	1.5	1
49	Behavior of GaN nanoneedles grown by using hydride vapor phase epitaxy for different growth times. Journal of the Korean Physical Society, 2015, 66, 1270-1274.	0.7	1
50	Pole figure measurement of the initial growth of GaN nanoneedles on GaN/Si(111) by using hydride vapor phase epitaxy. Journal of the Korean Physical Society, 2016, 69, 837-841.	0.7	1
51	Fabrication of Microholes in Silicon Wafers by Using Wet-Chemical Etching. New Physics: Sae Mulli, 2018, 68, 834-838.	0.1	1
52	Comparison of two schemes for cyclotron transition absorption line-widths in Ge and Si. Zeitschrift FÃ¼r Physik B-Condensed Matter, 1996, 100, 613-617.	1.1	0
53	Fabrication of the CuInGaSe Pellet and Characterization of the Thin Film. Japanese Journal of Applied Physics, 2011, 50, 01AG01.	1.5	0
54	Ultraviolet Light Emitting Diode with High Quality Epilayer Grown by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 01AG01.	1.5	0

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55	Growth of GaN on Metallic Compound Graphite Substrate Using Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 11NG03.	1.5	0
56	Carbon microspheres grown by using hydride vapor phase epitaxy. Journal of the Korean Physical Society, 2015, 67, 1268-1272.	0.7	0
57	Electrode-Evaporation Method of III-nitride Vertical-type Single Chip LEDs. Journal of the Korean Physical Society, 2018, 73, 1346-1350.	0.7	0
58	Comparison of AlN Nanowire-Like Structures Grown by using Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2019, 75, 242-247.	0.7	0
59	A Method to Enhance the Electric Field Intensity in a Gold Sub-microhole by Adding Copper Microspheres. Journal of the Korean Physical Society, 2019, 74, 111-115.	0.7	0
60	Growth of a Thick AlN Epilayer by Using the Mixed-Source Hydride Vapor Phase Epitaxy Method. Journal of the Korean Physical Society, 2020, 77, 282-287.	0.7	0
61	Optical Properties of Wurtzite ZnO-based Quantum Well Structures with Piezoelectric and Spontaneous Polarizations. , 2011, , 273-300.		0
62	Simulation for Improving the Light Extraction Efficiency of a GaN-based Light-emitting Diode via a Truncated Cone-shaped Pattern. New Physics: Sae Mulli, 2014, 64, 801-805.	0.1	0
63	Effects of Solvents in the Fabrication of a Hybrid Optical Device Based on GaN and MEH-PPV. New Physics: Sae Mulli, 2015, 65, 14-20.	0.1	0
64	Growth of a HVPE-AlGaN Epilayers with High Al Contents on Si (111) Substrates. New Physics: Sae Mulli, 2016, 66, 1106-1111.	0.1	0
65	Growth of an AlN Epilayer on a Patterned Sapphire Substrate by Using Mixed-Source HVPE. New Physics: Sae Mulli, 2016, 66, 1391-1396.	0.1	0
66	Atomic Arrangements and Orientations of Aligned Gallium-Nitride Nanoneedles Grown by Using Hydride Vapor Phase Epitaxy. New Physics: Sae Mulli, 2017, 67, 30-35.	0.1	0
67	Development of a Blue Light-Emitting Diode by Using a Mixed-Source Hydride-Vapor-Phase Epitaxy Method. New Physics: Sae Mulli, 2017, 67, 444-450.	0.1	0
68	Effect of Mixed Ga Metal for AlN Growth by Using Hydride Vapor-Phase Epitaxy. New Physics: Sae Mulli, 2017, 67, 1058-1065.	0.1	0
69	Vertical-Type Phosphor-Free White-Light-Emitting Diode Fabricated by Using a Mixed-Source Hydride Vapor-Phase Epitaxy Method. New Physics: Sae Mulli, 2018, 68, 742-748.	0.1	0
70	Characteristics of Copper Microspheres Grown by Using Mixed-Source Hydride Vapor-Phase Epitaxy. New Physics: Sae Mulli, 2018, 68, 1052-1058.	0.1	0